



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H1959

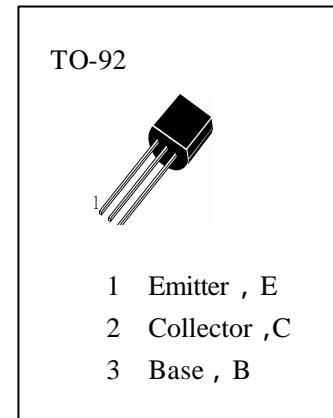
NPN EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY LOW POWER AMPLIFIER APPLICATIONS.

DRIVER STAGE AMPLIFIER APPLICATIONS.SWITCHING APPLICATIONS.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_c —Collector Dissipation.....	500mW
V_{CBO} —Collector-Base Voltage.....	35V
V_{CEO} —Collector-Emitter Voltage.....	30V
V_{EBO} —Emitter-Base Voltage.....	5V
I_c —Collector Current.....	500mA
I_b —Base Current.....	100mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			0.1	μA	$V_{CB}=35V, I_E=0$
I_{EBO}	Emitter Cut-off Current			0.1	μA	$V_{EB}=5V, I_C=0$
HFE	DC Current Gain	70		400		$V_{CE}=1V, I_C=100mA$
		25				$V_{CE}=6V, I_C=400mA$
V_{BE}	Base- Emitter Voltage		0.8	1	V	$V_{CE}=1V, I_C=100mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.1	0.25	V	$I_C=100mA, I_B=10mA$
f_T	Transition frequency		300		MHz	$V_{CE}=6V, I_C=20mA$
C_{ob}	Collector Output capacitance		7		pF	$V_{CB}=6V, I_E=0,$ $f=1MHz$

h_{FE} Classification

$h_{FE} (1)$	0	γ	GR
	70—140	120—240	200—400
$h_{FE} (2)$	0	γ	
	25 (Min)	40 (Min)	



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